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MOS FET

FCAB22370L1

Panasonic

FCAB22370L1

Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

■ Features

- Low source-source ON resistance:Rss(on) typ. = 3.3 m Ω (VGS = 3.8 V)
- · CSP(Chip Size Package)
- RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: 3P

■ Packaging

Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

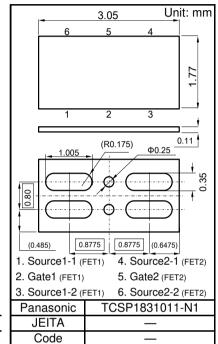
Parameter	Symbol	Rating	Unit
Source-source Voltage	VSS	20	V
Gate-source Voltage	VGS	±12	٧
Source Current (DC) *1	IS	10	Α
Source Current (Pulsed) *1,*2	ISp	100	Α
Total Power Dissipation *1	PD	0.45	W
Channel Temperature	Tch	150	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Thermal Resistance (ch-a)	Rth(ch-a)	278	°C/W

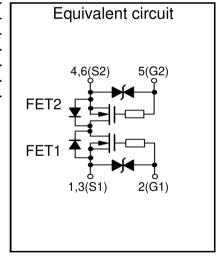
Note *1 Mounted on FR4 board ($25.4~\text{mm} \times 25.4~\text{mm} \times t1.0~\text{mm}$) using the minimum recommended pad size ($36\mu\text{m}$ Copper).

Established: 2015-10-23

Revised

: ####-##-##





^{*2} $t = 10 \mu s$, Duty Cycle $\leq 1 \%$

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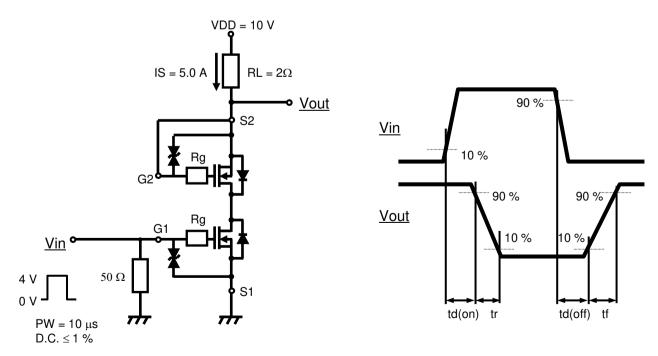
■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit	
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	20			V	
Zero Gate Voltage Source Current	ISSS	VSS = 20 V, VGS = 0 V			1.0	μΑ	
Gate-source Leakage Current	IGSS	$VGS = \pm 8 \text{ V}, VSS = 0 \text{ V}$			±10		
		$VGS = \pm 5 V$, $VSS = 0 V$			±1.0	μΑ	
Gate-source Threshold Voltage	Vth	IS = 1.41 mA, VSS = 10 V	0.35	0.90	1.4	V	
Source-source On-state Resistance	RSS(on)1	IS = 5.0 A, VGS = 4.5 V	2.1	3.1	4.2	mΩ	
	RSS(on)2	IS = 5.0 A, VGS = 3.8 V	2.2	3.3	4.3		
	RSS(on)3	IS = 5.0 A, VGS = 3.1 V	2.4	3.8	6.0		
	RSS(on)4	IS = 5.0 A, VGS = 2.5 V	2.6	4.6	9.0		
Body Diode Forward Voltage	VF(s-s)	IF = 5.0 A, VGS = 0 V		0.8	1.2	V	
Input Capacitance *1	Ciss			3700			
Output Capacitance *1	Coss	VSS = 10 V, VGS = 0 V, f = 1 kHz		380		pF	
Reverse Transfer Capacitance *1	Crss			340			
Turn-on delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		0.9		0	
Rise Time *1,*2	tr	IS = 5.0 A		2.0		μS	
Turn-off delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V 6			0		
Fall Time *1,*2	tf	IS = 5.0 A		3.7		μS	
Total Gate Charge *1	Qg	VDD = 10 V		33			
Gate-source Charge *1	Qgs	VGS = 0 to 4.0 V, IS = 5.0 A		11		nC	
Gate-drain Charge *1	Qgd			9			
Gate Resistance*1	Rg	f = 1 kHz	400	700	1000	Ω	

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

- *1 Guaranteed by design, not subject to production testing
- *2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

Note2: Measurement circuit



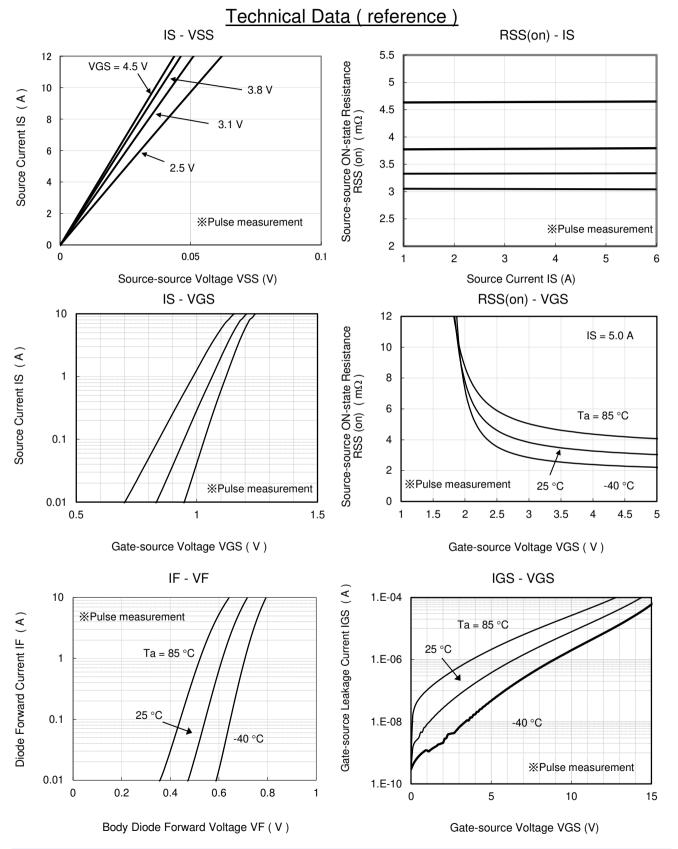
Page 2 of 5

Established : 2015-10-23 Revised : ###-##-##

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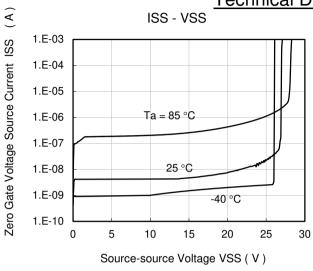
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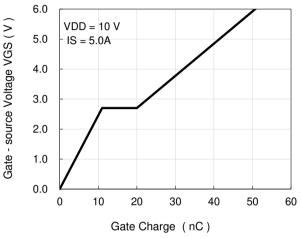
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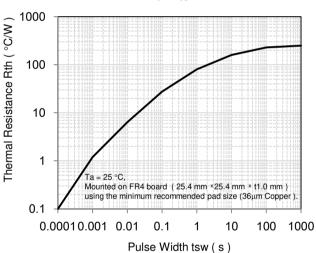




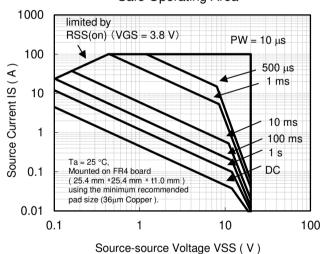
Dynamic Input/Output Characteristics



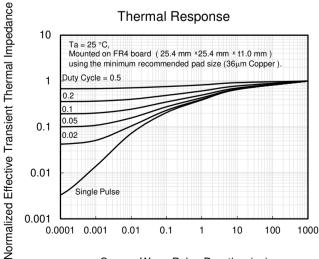




Safe Operating Area



Thermal Response



Square Wave Pulse Duration (s)

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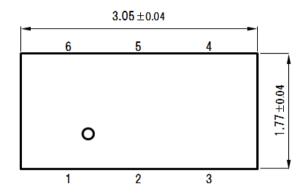
Panasonic

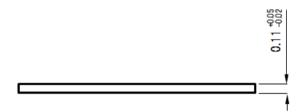
MOS FET

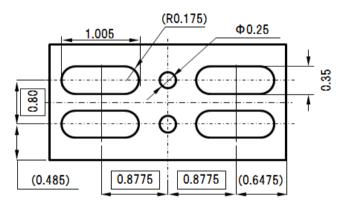
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■ Outline (TCSP1831011-N1)

Unit: mm

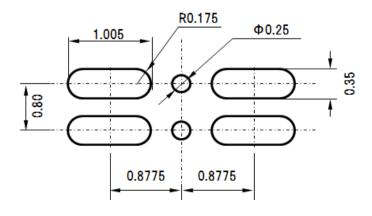






■ Land Pattern (Reference)

Unit: mm



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